Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt®

Anode



- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- · Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use as clamp, snubber and freewheeling diode in a flyback aux power supplies, bootstrap and desaturate for HV MOSFET and IGBT driver, high frequency rectifiers in a cuk and sepic circuit for LED lighting.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		1200	V			
Average rectified forward current	I _{F(AV)}	T _{SP} = 142 °C, D = 0.5	1	^			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 8.3 ms sine pulse	21	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C			



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SMA (DO-214AC)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	1 A				
V _R	1200 V				
V _F at I _F	1.33 V				
t _{rr}	45 ns				
T _J max.	175 °C				
Package	SMA (DO-214AC)				
Circuit configuration	Single				

HALOGEN



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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	1200	-	-		
		I _F = 1 A	-	1.75	2.25	v	
Forward voltage drop	V _F	I _F = 1 A, T _J = 125 °C	-	1.40	1.65	v	
		I _F = 1 A, T _J = 150 °C	-	1.33	1.55		
Reverse leakage current	1	$V_{R} = V_{R}$ rated	-	-	5	μA	
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	50	μA	
Junction capacitance	CT	V _R = 1200 V, 1 MHz	-	3.5	-	pF	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	YMBOL TEST CONDITIONS MIN. TYP				MAX.	UNITS	
		$I_{\rm F} = 0.5 \text{ A}, I_{\rm R} = 1 \text{ A}$	A, I _{rr} = 0.25 A	-	35	45		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	90	-	ns	
		T _J = 125 °C		-	110	-		
Peak recovery current	1	T _J = 25 °C	$I_F = 1 A,$ $dI_F/dt = 200 A/\mu s,$	-	3	-	А	
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	4	-	A	
	0	T _J = 25 °C		-	95	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	190	-	no	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C		
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	15	18	°C/W		
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with recommended pad size	-	110	-	°C/W		
Approximate weight				0.07		g		
Marking device		Case style SMA (DO-214AC)		1>	(12			

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)

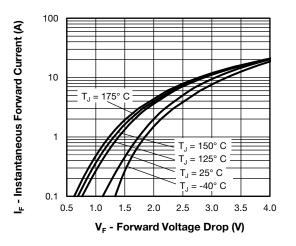


Fig. 1 - Typical Forward Voltage Drop Characteristics

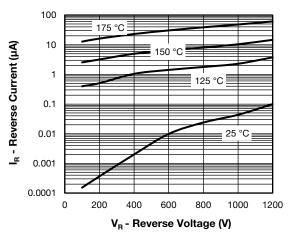


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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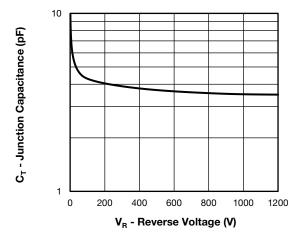


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

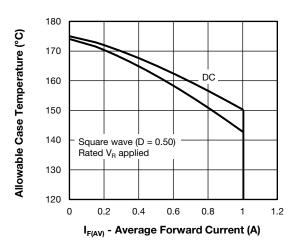


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

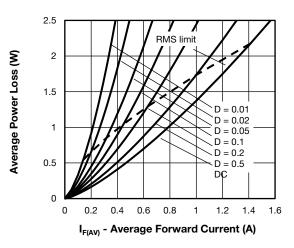


Fig. 5 - Forward Power Loss Characteristics

120 I_F = 1 A, V_R = 800 V 100 125 °C 80 t_{rr} (ns) 25 °C 60 40 20 200 300 400 500 600 dl_F/dt (A/µs)

Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

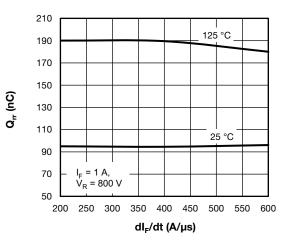


Fig. 7 - I_{rr} (A) vs. dI_F/dt

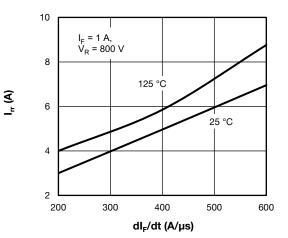


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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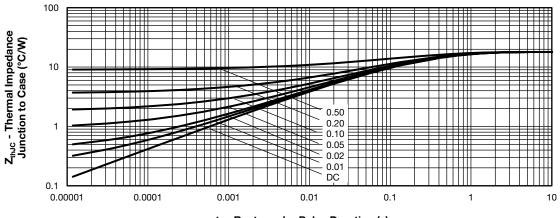
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VS-E7MX0112-M3

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t₁ - Rectangular Pulse Duration (s)

Fig. 9 - Transient Thermal Impedance, Junction to Case

ORDERING INFORMATION TABLE

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SHA

Device code	VS-	E	7	м	x	01	12	-M3	
	1	2	3	4	5	6	7	8	
	2	- Circ E = - 7 =	cuit conf single o FRED g	generatio	n:	oduct			
	4 5	- Pro	: SMA p cess typ hyperfa	0	very				
	6	- Cur	rent rati	ng (01 =	= 1 A)				
	7	- Vol	tage coo	de (12 =	1200 V)			
	8	M3	s = halog	gen-free	, RoHS-	complia	ant, and	termina	tions lead

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-E7MX0112-M3/I	7500	7500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95400				
Part marking information	www.vishay.com/doc?95472				
Packaging information	www.vishay.com/doc?95404				

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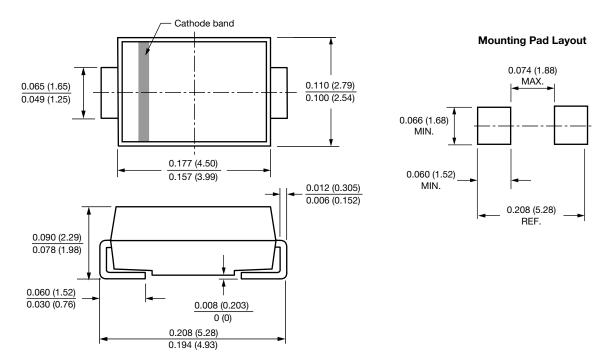
Outline Dimensions

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SMA

DIMENSIONS in inches (millimeters)

DO-214AC (SMA)





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